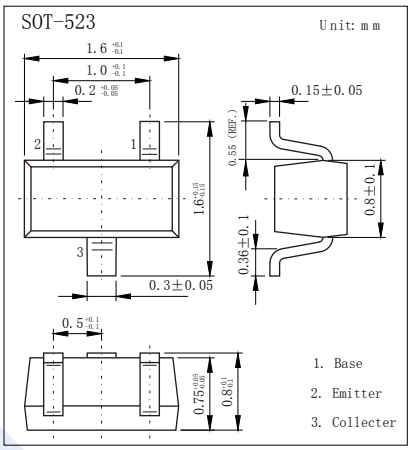
PNP Transistors
BC857T (KC857T)



■ Features

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-50	V
Collector - Emitter Voltage	V_{CEO}	-45	
Emitter - Base Voltage	V_{EBO}	-6	
Collector Current - Continuous	I_C	-0.1	A
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-50			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -10 mA, I_B=0	-45			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C=0	-6			
Collector-base cut-off current	I_{CBO}	V_{CB}= -50 V , I_E=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -6V , I_C=0			-0.1	uA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10 mA, I_B=-0.5mA			-0.3	V
		I_C=-100 mA, I_B=-5mA			-0.65	
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-10 mA, I_B=-0.5mA		-0.7		
		I_C=-100 mA, I_B=-5mA		-0.9		
Base-emitter voltage	$V_{BE(on)}$	V_{CE}= -5V, I_C= -2mA	-0.6		-0.75	
		V_{CE}= -5V, I_C= -10mA			-0.82	
DC current gain	h_{FE}	V_{CE}= -5V, I_C= -2mA	125		800	
Noise figure	NF	V_{CE}=-5V,f=1MHz,Ic=0.2mA Rs=2KΩ,BW=200HZ			10	dB
Collector output capacitance	C_{ob}	V_{CB}= -10V,f=1MHz			4.5	pF
Transition frequency	f_T	V_{CE}= -5 V,I_C=-10mA,f=100MHz	100			MHz

■ Classification of hfe

Type	BC857AT	BC857BT	BC857CT
Range	125-250	220-475	420-800
Marking	3E	3F	3G